

IN THE SPECIFICATION

Please replace paragraph 0030 on page 7 with the following:

Now, isotropic etching is used to etch the epitaxial layer 23 in alignment with the spacers 32. This again may be a plasma etching process. An etchant that discriminates between the oxide and silicon is used. This results in a thinning of the epitaxial layer 23 as shown by the dimension 35 of Figure 9, and an undercutting of the spacers ~~[[23]]~~ 32 as shown by the undercut 36 of Figure 9. Note that during this etching, the hard mask 22 protects the polysilicon pedestal 28. Also note, the oxide regions 25 disposed under the pedestal 28 prevent the formation of a parasitic path between the pedestal and the layer 23. While the undercutting 36 is shown to have a vertical surface, it may be slightly curved, with more of an undercut at the upper section. The etching chemistry may be adjusted to keep this undercut as vertical as possible.